NSN 5961-01-439-2392

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Inclosure Material:

Ceramic

Overall Length:

0.180 inches

Overall Height:

0.065 inches

Overall Width:

0.180 inches

End Application:

An/prc-11 (v) e/i fscm 04655

Internal Configuration:

Field effect

Mounting Method:

Compression

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

30.0 drain to gate voltage and 30.00 drain to source voltage and 30.0 drain to substrate voltage

Current Rating Per Characteristic:

50.00 milliamperes source cutoff current of standard range

Power Rating Per Characteristic:

1.2 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Precious Material And Location:

Plated leads gold

Test Data Document:

04655-13-2728240 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 case

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0